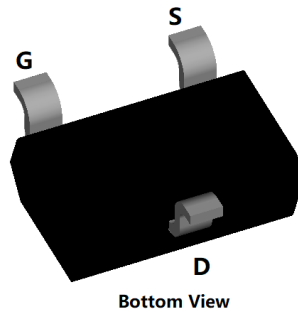
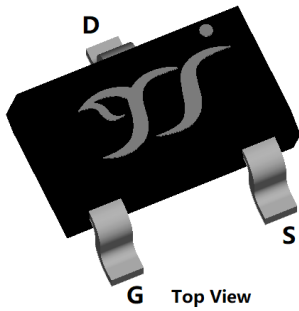
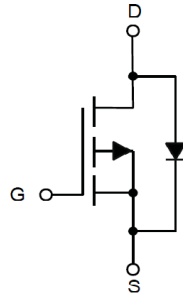


P-Channel Enhancement Mode Field Effect Transistor



SOT-23-3L



Product Summary

- V_{DS} -30V
- I_D -4.4A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) <55mohm
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) <66mohm
- $R_{DS(ON)}$ (at $V_{GS}=-2.5V$) <94mohm
- 100% ∇V_{DS} Tested

General Description

- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Applications

- Battery protection
- Power management
- Load switch

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	-30	V
Gate-source Voltage	V_{GS}	± 12	V
Drain Current	I_D	$T_A=25^\circ C$	-4.4
		$T_A=70^\circ C$	-3.5
Pulsed Drain Current ^A	I_{DM}	-27	A
Total Power Dissipation	P_D	$T_A=25^\circ C$	1.5
		$T_A=70^\circ C$	0.98
Thermal Resistance Junction-to-Ambient ^B	$R_{\theta JA}$	82	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3401AL	F2	R1 _A .	3000	30000	120000	7" reel



YJL3401AL

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.6	-0.9	-1.4	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-4.4A		40	55	mΩ
		V _{GS} =-4.5V, I _D =-3A		47	66	
		V _{GS} =-2.5V, I _D =-2A		60	94	
Diode Forward Voltage	V _{SD}	I _S =-4.4A, V _{GS} =0V			-1.2	V
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, f=1MHZ		1040		pF
Output Capacitance	C _{oss}			80		
Reverse Transfer Capacitance	C _{rss}			68		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DS} =-15V, I _D =-4.4A		22		nC
Gate-Source Charge	Q _{gs}			3.28		
Gate-Drain Charge	Q _{gd}			2.11		
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V, V _{DS} =-15V, I _D =4.4A R _{GEN} =3Ω		4.4		nC
Turn-on Rise Time	t _r			26		
Turn-off Delay Time	t _{D(off)}			49.2		
Turn-off fall Time	t _f			42.8		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design, while R_{θJA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



■ Typical Performance Characteristics

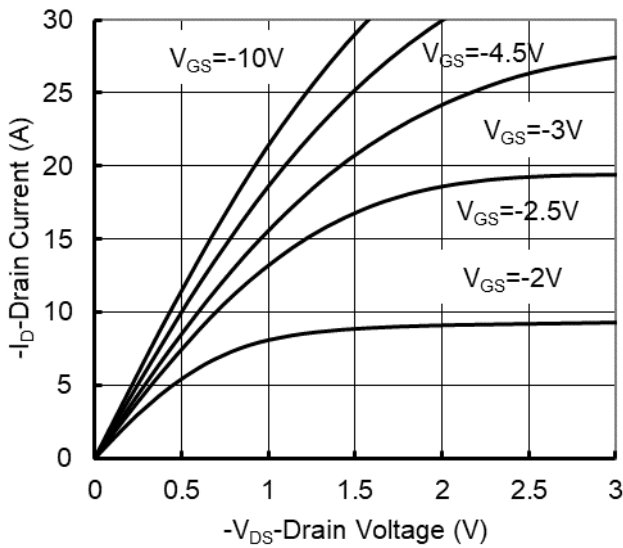


Figure1. Output Characteristics

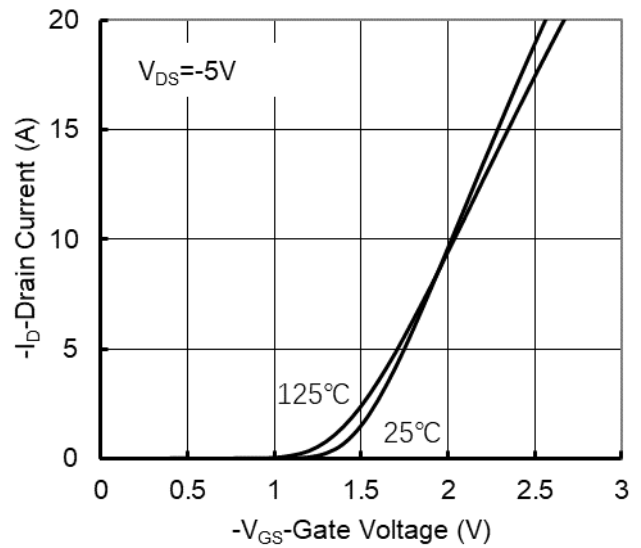


Figure2. Transfer Characteristics

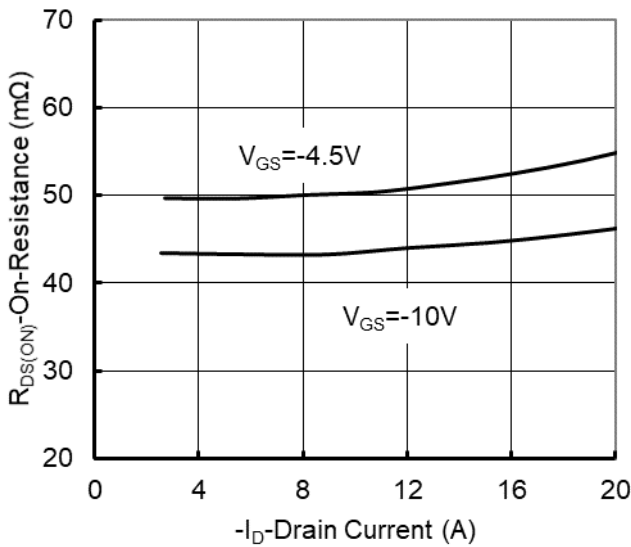


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

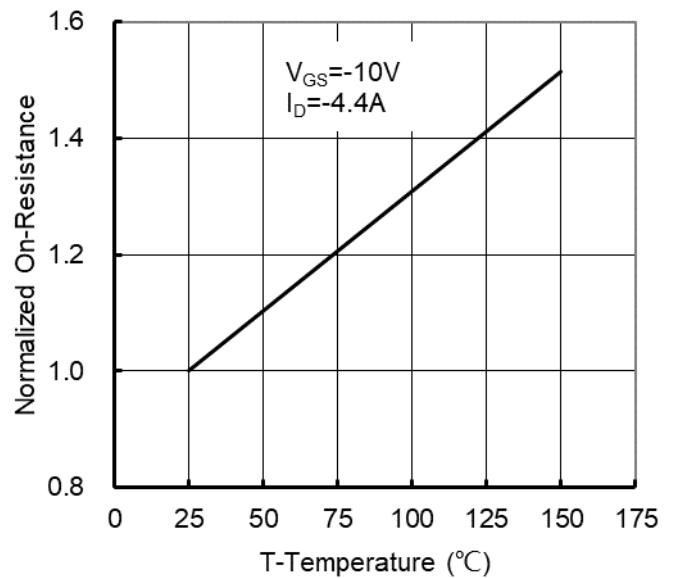


Figure 4: On-Resistance vs. Junction Temperature

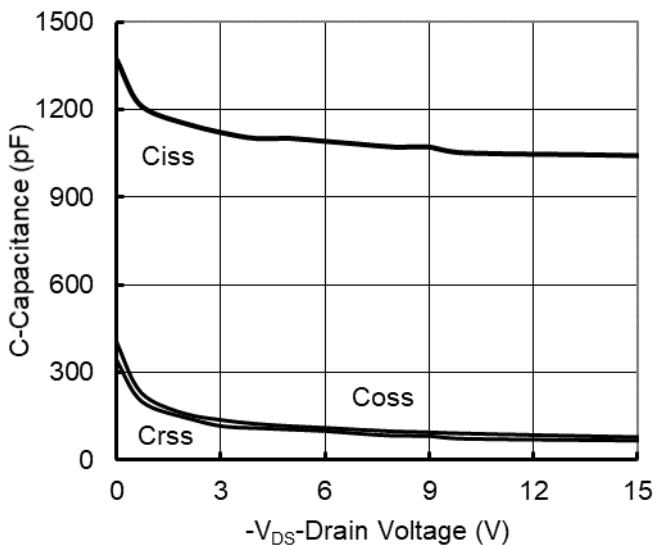


Figure5. Capacitance Characteristics

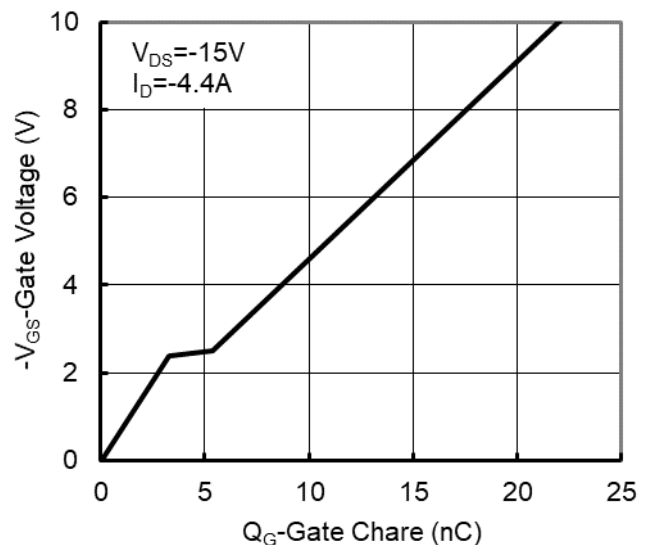


Figure6. Gate Charge

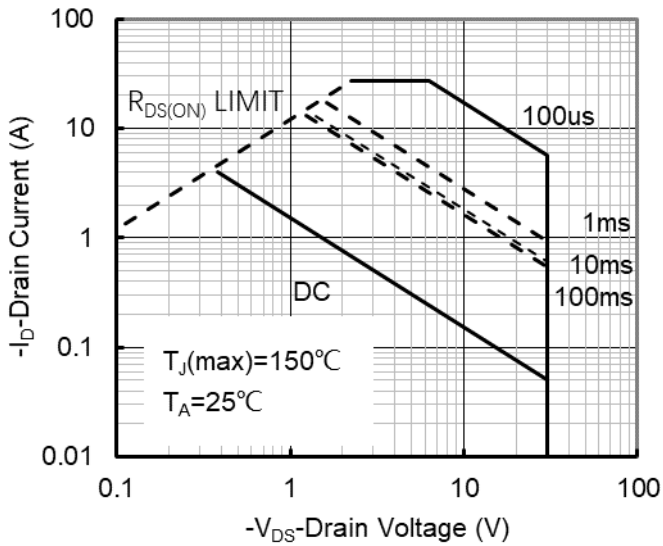


Figure7. Safe Operation Area

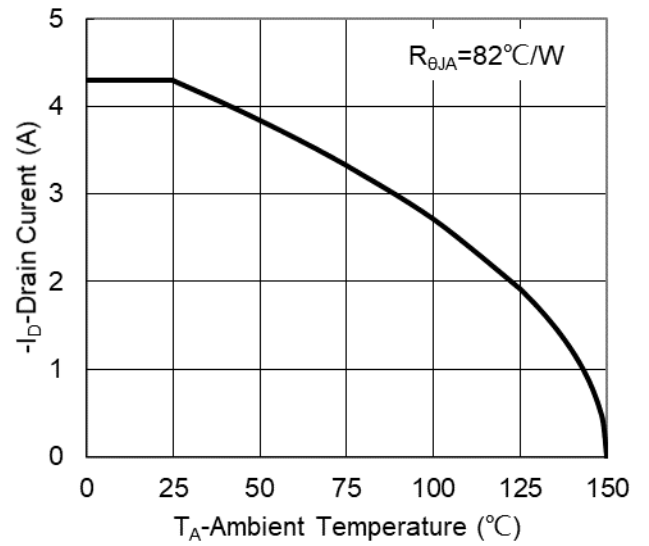


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

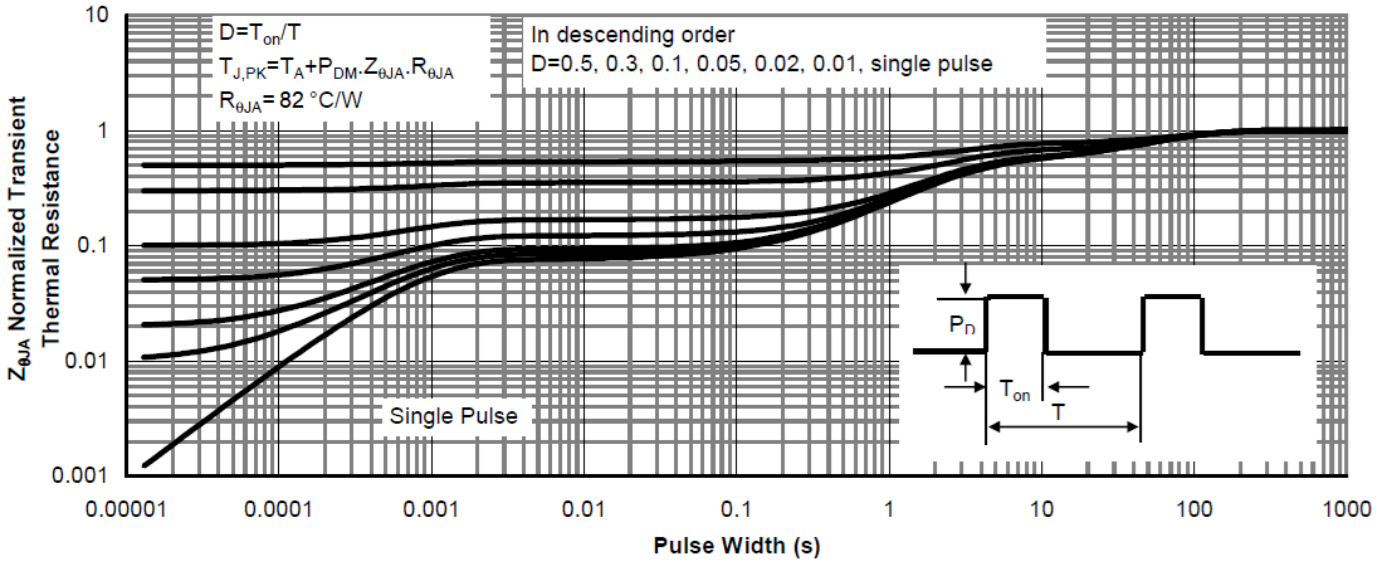
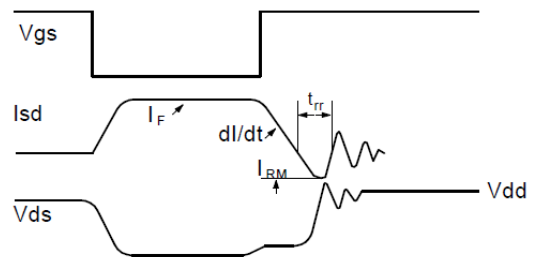
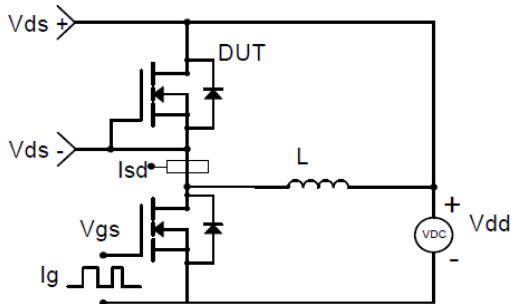


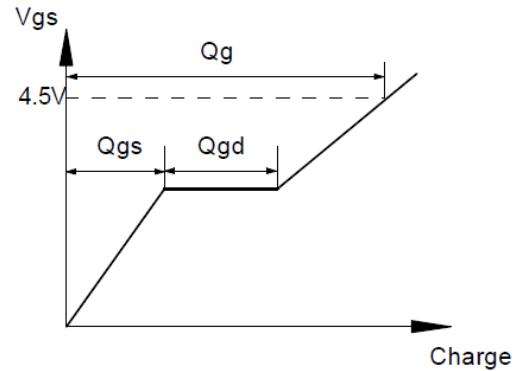
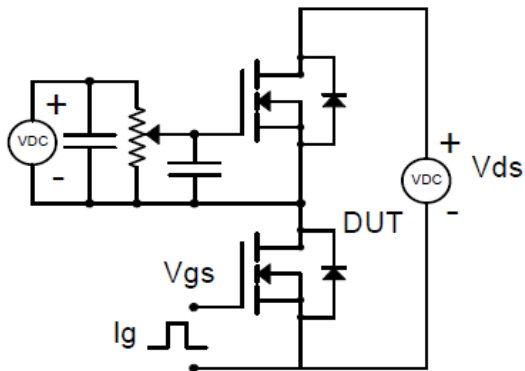
Figure9. Normalized Maximum Transient Thermal Impedance



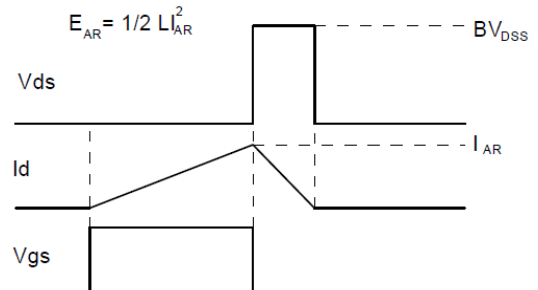
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

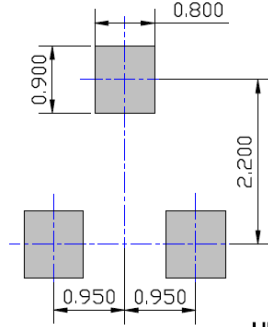
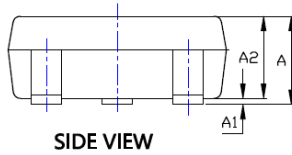
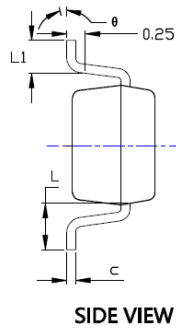
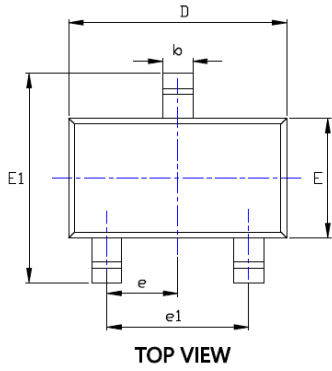


Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

■ SOT-23-3L Package Information



UNIT: mm

SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.041	0.049	1.050	1.250
A1	0.000	0.008	0.000	0.200
A2	0.041	0.045	1.050	1.150
b	0.012	0.020	0.300	0.500
c	0.004	0.008	0.100	0.200
D	0.111	0.119	2.820	3.020
E	0.059	0.067	1.500	1.700
E1	0.104	0.116	2.650	2.950
e	0.037TYP		0.950TYP	
e1	0.071	0.079	1.800	2.000
L	0.024REF		0.600REF	
L1	0.012	0.024	0.300	0.600
∅	0°	8°	0°	8°

NOTE:
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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